ROCHESTER INSTITUTE OF TECHNOLOGY MICROELECTRONIC ENGINEERING

Introduction to MESA

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Revision Date: 6-20-2013 LEC_MESA.PPT

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OUTLINE

Introduction to MESA Hardware **Software User Interface MESA Factory Organization Operations Processes Products** Masks **Data Base Query Reports SPC** Charts Homework

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MESA - MANUFACTURING EXECUTION SYSTEM APPLICATION

MESA is an integrated relational database system for discrete part manufacturing (a computerized record-keeping system)

A relational database system is a database in which the data is perceived by the user as tables (and nothing but tables)

Operations include:

Adding new tables to the database Inserting new data into existing tables Retrieving data from existing tables Updating data in existing tables Deleting data from existing tables Removing existing tables from the database Quarrying database tables for specific information

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MES CIM SYSTEMS



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CIM SYSTEM

- § AS/400
- § Qty 10 PC Workstations
- § Ethernet LAN
- § Quality Analyst Software
- § MESA Software (Manufacturing Execution System Application)
 - **§ Work-in-process Tracking**
 - § Transaction Processing
 - § Production Costs
 - § Scheduling
 - § Statistical Process Control
 - § Resource Management

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§ On-Line Reporting Lot Status Transaction History Data Collection Specifications and Instructions

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CIM SYSTEM - PC WORKSTATION



ACCESS TO AS-400 AND MESA

The computers in the clean room have an icon on the desktop that will connect the user to the AS400 sign on screen:





Username is STUDENT password is NIGHTSHIFT

Next the user signs on to the MESA software:

Username is OPERATOR password is OPERATOR

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START UP REMOTE DESKTOP



Int	roduction to MESA
LOG ON TO K	IF SERVER, START UP MESA
Remote Desktop Connection Remote Desktop Connection	Type in kgcoe-kif.main.ad.rit.edu
Computer: <u>kgcoe-kif, main, ad. rit, edu</u> User name: MAIN\lifeee You will be asked for credentials when you connect.	Click Connect
Image: Connect Connect	ame and Password dents should have this)
Then: Click on MESA I	con Sign onto AS400:
Microelectronic Engineering	System: HOST400 User ID: STUDENT STUDENT NIGHTSHIFT
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OPERATOR USER INTERFACE



ENGINEER USER INTERFACE

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FACULTY USER INTERFACE





RESOURCE HIERARCHY



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OPERATIONS

CL01	RCA Clean	IM01	ion implant wafers
CV01	LPCVD Polysilicon	ME01	sputter aluminum
CV02	LPCVD Silicon Nitride	OX01	wet oxide 5000 A
CV03	LPCVD Low Temperature Oxide	OX02	dry oxide 600 A
DE01	Four point probe	OX03	dry oxide and anneal
DI01	p-type spin on diffusion	OX04	wet oxide
DI02	p-type spin on plus oxide growth	OX05	dry oxide with TCA clean
DI03	p-type from solid BN source	OX06	dry oxide with TCA
DI04	n-type spin on diffusion	OX07	post implant anneal
DI05	n-type from solid P source	OX08	100 A tunnel oxide
DI06	n-type spin on arsenic source	PH01	1X Contact Printer
ET01	control wafer oxide step etch	PH03	Photolithography on Stepper
ET02	oxide etch until pull dry	SI01	Sinter
ET07	photoresist strip in asher	TE01	Test van der pauw, CBKR
ET08	plasma etch polysilicon	TE02	Test transistors
ET09	plasma etch silicon nitride	TE03	Test integrated circuits
ET10	plasma etch oxide	GR01	groove and stain
\frown	-	ID01	scribe wafers

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MASKS

PROCESS MASK LEVEL NAMES MASK SET NAME (DEFINES THE PRODUCT) '→ MASK ID'S **EXAMPLE: CMOS PROCESS LEVEL NAMES:** CMOSWELL **PRODUCT: GATE ARRAY CMOSACTIVE MASKSET NAME: E951FACLFX CMOSSTOP** E951FACLF1 **CMOSVT** E951FACLF2 **CMOSPOLY** E951FACLF3 **CMOSN+DS** E951FACLF4 **CMOSP+DS** E951FACLF5 **CMOSCC** E951FACLF6 **CMOSMETAL1** E951FACLF7 E951FACLF8 **Rochester Institute of Technology Microelectronic Engineering** E951FACLF9



TABLES (FILES)

In the Mesa Database Library (MESADB) there are over 200 File names (TABLES) with descriptions such as:

LTLLH100 Lot History LTLMD101 MESA Move Detail/UDC x Lot/Oper/Step/Date/Time LTLMD103 MESA Move Detail/UDC x Oper/Date/Time LTPMD100 MESA Move Detail LTPMS100 MESA Maskset Name LTLLG102 MESA Lot Genealogy by transaction date/time LTLLT105 MESA Lot Master x Original Lot/Start date

etc.

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FIELD NAMES (COLUMNS) & RECORDS (ROWS)

Each file has fields (columns) defined for storage of data in a record (row). In the LTPMD100 file called MESA Move Detail there are about 70 fields. Some are listed below:

MDTRCD Transaction Code MDLOT Lot Number MDTRYR **Transaction Year MDUSER** User ID **MDTOOP** To operation **MDFSTP** From process step User defined field 1 MDUD1 **MDPRC** Process

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etc



FILE SELECTIONS

File =	LTLMD101
Library =	MESADB
Member =	*FIRST
Format =	LTFMD101

MESA has over 200 File names with descriptions such as: LTLLH100 Lot History File LTLMD101 MESA Move Detail/UDC x Lot/Oper/Step/Date/Time LTLMD103 MESA Move Detail/UDC x Oper/Date/Time LTPMD100 MESA Move Detail LTPMS100 MESA Maskset Name File

These files can be joined in various ways



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SELECT FIELDS

Order	Code	Description	Len	Dec
10	MDFSTP	Mesa Database From Step	6	2
20	MDFROP	Mesa Database From Operation	4	0
30	DATE	DATE as defined	6	0
40	MDLOT	Mesa Database Lot Number	10	0
50	COUNT1	UDN01*	6	0
60	COUNT2	UDN02*	6	0
70	XOX	UDN03*	4	0
80	PADOX	UDN03*	4	0

etc.



* user defined numeric parameter 01, 02, etc up to 18

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SELECT SORT FIELDS

PRIORITY A/D 10 A MDFSTP 20 A DATE 30 D MDLOT

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OTHER

> Select collating sequence (Ascending, Descending) > Specify report column formatting (Column Heading, Number of characters, etc.) > Select report summary functions (Total, Average, Minimum, Maximum, Count) > Define report breaks (new page after each sort field, etc) > Select output type and output form (printed, to display, etc.) > Specify processing options (batch, interactive, ...)

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EMPLOYEE MOVES EXAMPLE

QUENI MAME:	EMPLOY	YEE		LIBRARY:MESADB
FILE: LTLMD101			FORMA	T:LTFMD101
RESULT FIELDS:				
SELECT RECORI	DS:	MDLOT	LIKE	'F%'
1	AND N	IDMVTP	EQ	'1'
1	AND N	IDTRTM	GŤ	8
1	AND N	IDTRYR	GT	98
1	AND N	IDEMPLIST	'LFFEE	E' 'KDHEMC' 'KEBEM(
	IV M M M	IDTRYK IDTRMO IDTRDY IDFROP		1=101AL 2=AVE 3=MIN 4=MAX 5=COUNT
REPORT COLUM REPORT BREAKS	N FORMA S:	ATTING AND SU	MMARY	FUNCTIONS:

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QUERY DEFINITION TO FIND SETUP AND RUN TIMES FOR ALL FACTORY OPERATIONS



QUERY DEFINITION FOR CMOS PROCESS DATA



DATA

	;;											
DATA UP TO 9-15-9	97											
Parameter Name	Units											
Alignment Oxide	Å	6900	4846	4941	4097	4282	5243	4035	5449	4928	4505	4905
Pad Oxide	Å	511	530	594	481	514	500	490	365	479	484	522
Nitride Thickness	Å	1535	1570	1850	1850	1690	1737					
Field Oxide Thicknes	Å	10874	9660	10443	10489	9546	10711	10743	11651	9455	11357	10987
Photo x-overlay	μm	2	1	1	2	1	2	-1	1	-1	0	(
Photo y-overlay	μm	1	1	1	0	2	0	1	-1	-1	-1	(
Kooi Oxide Thicknes	Å	804	399	750	902	814	717	230	1056	981	1200	869
Gate Oxide	Å	601	494	503	484	443	430	503	495	499	508	496
Poly Thickness	Å	5723	6272	6635	6652	6442	7185	6089	4383	5656	4607	5107
Poly Sheet Rho	Å	24	32	18	27	72	55	16	15	22	32	15
LTO Thickness	Å	4570	2282	3166	4913	3724	7356	5318	4616	6700	4479	3386
Metal Thickness	Å	4000	5000	4000	2300	6500	7500					
Rho N+	ohms	21	22	28	27	24	33	17	24	25	22	20
Rho P+	ohms	44	91	36	70	54	28	25	25	35	26	23
Rho Well	ohms	973	1380	1250	1020	1360	1500	1260	2290			
Rho Metal	ohms	0.06	0.09	0.05	0.01	0.15	0.14	0.1	0.11	0.16		
Gc met-Poly	mho/µm2	0.03	0.02	0.023								
	Roc	hester Institu	te of Techno	ology								
	Mici	roelectronic	Engineering									
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REPORTS

TLOGRPT Transaction Log Report PSRTMNU Production Summary Report Menu PSBORPT Production Analysis LSRTMNU Lot Status Report Menu LSHPRPT Lot Ship Summary Report LSTRRPT Lot Start Summary Report

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STATISTICAL PROCESS CONTROL CHARTS

- 1. All Processes RCA Clean Particle Delta
- 2. PMOS/CMOS 5000 A Wet Oxide Thickness
- 3. P-well CMOS Well Drive-in Oxide Thickness
- 4. P-well CMOS Well Drive-in Rhos
- 5. P-well CMOS Well Drive-in Junction Depth
- 6. NMOS/CMOS Pad Oxide Thickness
- 7. All Processes Field Oxide Thickness
- 8. NMOS/CMOS Kooi Oxide Thickness
- 9. All Processes Gate Oxide Thickness
- 10. NMOS/CMOS Nitride Deposition Thickness
- 11. NMOS/CMOS Polysilicon Deposition Thickness
- 12. NMOS/CMOS Polysilicon Rhos
- 13. NMOS/CMOS Polysilicon Etch Rate
- 14. NMOS/CMOS Nitride Etch Rate
- 15. P-well CMOS N+ Rhos
- 16. P-well CMOS N+ Xj
- 17. P-well CMOS P+ Rhos
- 99. All Query Update may take 1 hour
- 18. P-well CMOS P+ Xj
- 19. All Processes Metal Thickness
- 20. P-well CMOS 4 um CD
- 21. P-well CMOS X&Y Overlay





SPC CHARTS



Statistical Process Control Charts (SPC Charts) combine a query with data analysis and plotting software.

North West Quality Analysis software is used at RIT to display the SPC Charts. We display a run chart (top), Histogram (bottom), Gaussian Model (Green), and Calculations of Mean, Standard Deviation, Cpk, Cp and other statistical parameters.

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SPC CHARTS CAN BE VIEWED AT MOVE-IN

PrtScrn Copy Paste Se	and Recv Display Color Map Record Stop Play Quit Clipbrd Support Index
9/09/07 6:11:23	MESA IGMSINQ S36801 Instruction Group Inquiry QPADEV0019 RIT
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	P/P 800C, RU 20min, soak ~54 min dry O2 1000C, RD 40min B.0 When wafers complete abort 250 and XRF idle recipe 999 B.0 Record soak temp and soak time
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SPC MAIN MENU





NWA QUALITY ANALYST, SPC CHART



Pad Oxide Target 500Å USL 600Å LSL 400Å Mean 535Å Std Dev 35Å Cpk 0.8648 Cp 1.332



REFERENCES

1. "MESA System Overview", Camstar Systems, Inc., 2105 South Bascom Avenue, Suite 200, Campbell, California 95008, Tel: (408) 59-5700, Fax: (408) 559-5719.

2. "AS/400 Query (Program 5728-QU1), Relese3, Modification 0", IBM Corporation, Department 245, 3605 North Highway 52, Rochester, MN 55901-9986.

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HOMEWORK – INTRO TO MESA

- **1. What are the components of a process definition?**
- 2. How is a product defined?
- 3. Give an example of a data base query?
- 4. What does MESA allow an Engineer to do that an Operator can not do?
- 5. Give a brief description of the following terms as they relate to the RIT Factory and CIM system. Give an example where it makes sense. Show a schematic diagram to illustrate hierarchical relationships for related items.

AS/400, Ethernet, Exit F3, Cancel F12, User ID, Operator, Integrated Relational Database, Resource, Work Center, Operation, Department, Plant, Resource Type, Resource Sub Type, Resource ID, Unit of Measure, User Defined Units of Measure, Start Code, Scrap Code, Bonus Code, Yield Loss Code, Hold Code, Operation, Process, Specification, Product, Product Class, Mask ID, Mask Level Names, Mask Set, Document, Step, Instruction Group, Parameter Group, Report, Listing, Inquiry, Query, Transaction

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